

ABSTRACT OF THE DISCLOSURE

The present invention provides a display device which can reduce the irregularities of characteristics of a pair of transistors which are prepared by a pseudo single crystallizing technique and are used in a differential amplifying circuit or the like. The display device includes semiconductor layers formed on a substrate and having pseudo single crystal regions and a plurality of thin film transistor arranged in the inside of the pseudo single crystal regions. Out of the plurality of thin film transistors, two or more thin film transistors which are required to exhibit small irregularities relative to each other as the characteristics of the transistors have the direction of a length of gates of the respective thin film transistors arranged with an inclination of within  $\pm 20$  degree with respect to the longitudinal direction of the strip-like grown crystals and are arranged such that when channel regions of the respective thin film transistors are imaginarily extended in parallel to the growth direction of the strip-like grown crystals, at least portions of the channel regions superpose each other.